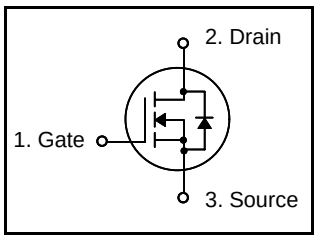
Pb Free Plating Product

IRFZ44N

50A,60V Heatsink Planar N-Channel Power MOSFET

Features

- 50A, 60V, $R_{DS(on)}$ = 0.022Ω @V_{GS} = 10 V
- Low gate charge (typical 31 nC)
- Low Crss (typical 65 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



BV_{DSS} = 60V

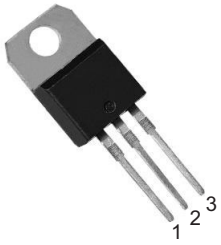
$R_{DS(ON)}$ = 0.022 ohm

I_D = 50A

General Description

This N-channel enhancement mode field-effect power transistor using THINKI Semiconductor advanced planar stripe, DMOS technology intended for off-line switch mode power supply.
Also, especially designed to minimize rds(on) and high rugged avalanche characteristics. The TO-220M-SQ pkg is well suited for adaptor power units,amplifiers,inverters and SMPS application.

TO-220M-SQ



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		IRFZ44N	Units
V_{DSS}	Drain-Source Voltage		60	V
I_D	Drain Current - Continuous (T_C = 25°C)		50	A
	Drain Current - Continuous (T_C = 100°C)		35.4	A
I_{DM}	Drain Current - Pulsed	(Note 1)	200	A
V_{GSS}	Gate-Source Voltage		± 25	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	490	mJ
I_{AR}	Avalanche Current	(Note 1)	50	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P_D	Power Dissipation (T_C = 25°C)		120	W
	- Derate above 25°C		0.8	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.24	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	60	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.06	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 48 V, T_C = 150°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 25 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -25 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 25 A	--	0.018	0.022	Ω
g_{FS}	Forward Transconductance	V_{DS} = 25 V, I_D = 25 A (Note 4)	--	22	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1180	1540	pF
C_{oss}	Output Capacitance		--	440	580	pF
C_{rss}	Reverse Transfer Capacitance		--	65	90	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30 V, I_D = 25 A, R_G = 25 Ω (Note 4, 5)	--	15	40	ns
t_r	Turn-On Rise Time		--	105	220	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Turn-Off Fall Time		--	65	140	ns
Q_g	Total Gate Charge	V_{DS} = 48 V, I_D = 50 A, V_{GS} = 10 V (Note 4, 5)	--	31	41	nC
Q_{gs}	Gate-Source Charge		--	8	--	nC
Q_{gd}	Gate-Drain Charge		--	13	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	50	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	200	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 50 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 50 A, dI_F / dt = 100 A/μs (Note 4)	--	52	--	ns
Q_{rr}	Reverse Recovery Charge		--	75	--	nC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 230μH, I_{AS} = 50A, V_{DD} = 25V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 50A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com

Typical Characteristics

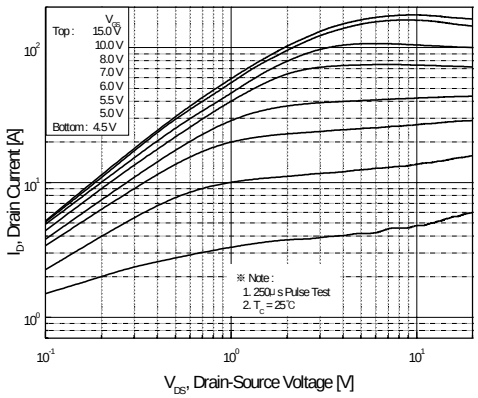


Figure 1. On-Region Characteristics

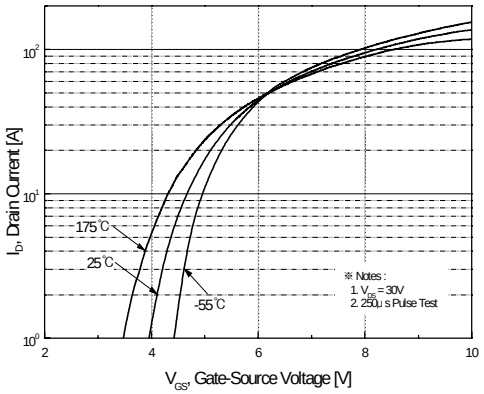


Figure 2. Transfer Characteristics

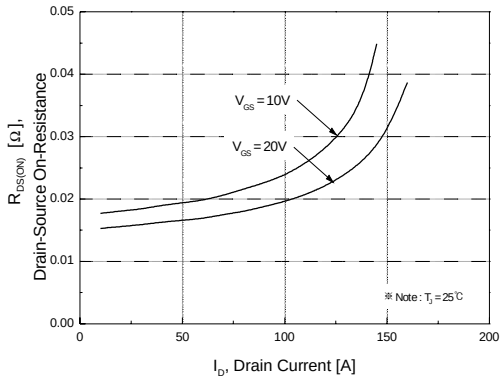


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

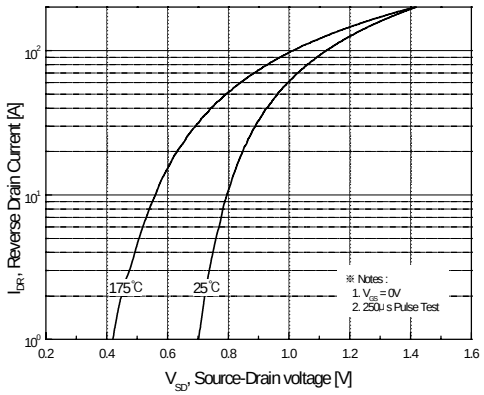


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

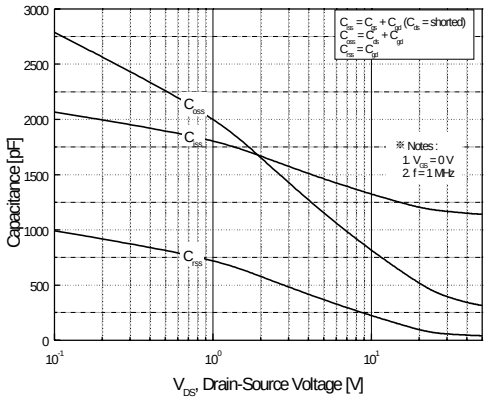


Figure 5. Capacitance Characteristics

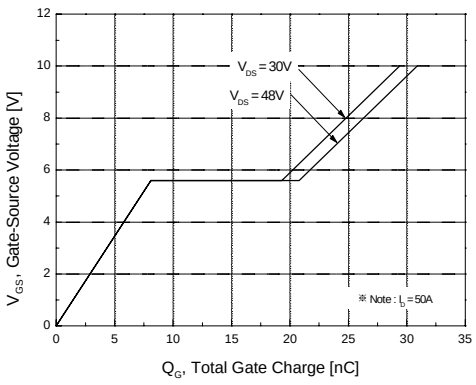


Figure 6. Gate Charge Characteristics

© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com

Typical Characteristics (Continued)

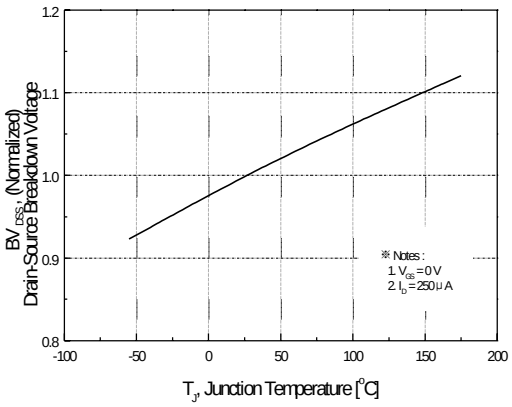


Figure 7. Breakdown Voltage Variation vs. Temperature

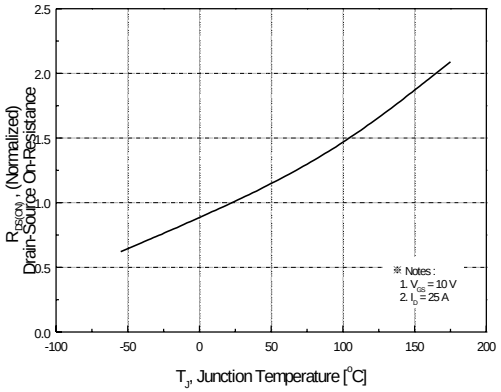


Figure 8. On-Resistance Variation vs. Temperature

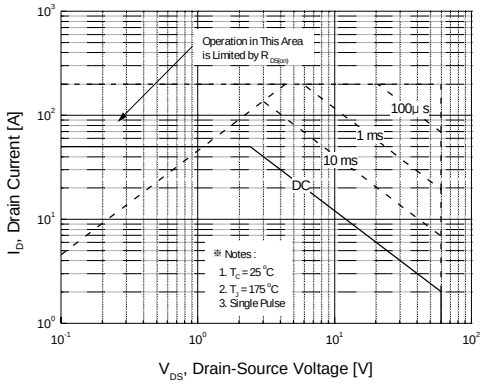


Figure 9. Maximum Safe Operating Area

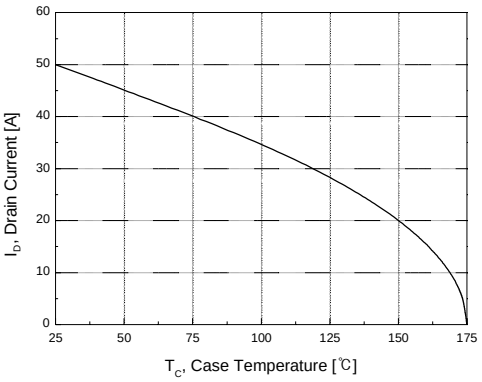


Figure 10. Maximum Drain Current vs. Case Temperature

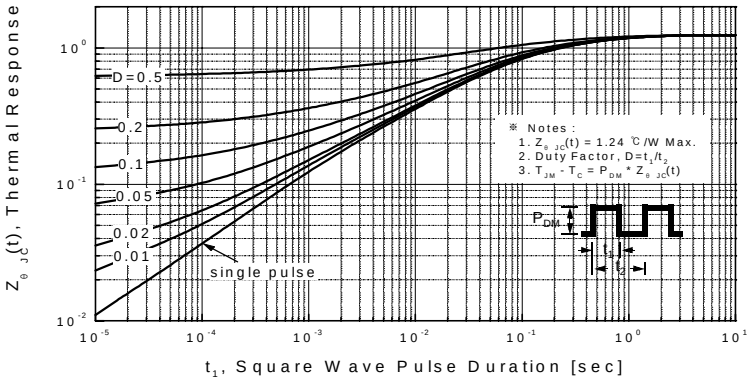
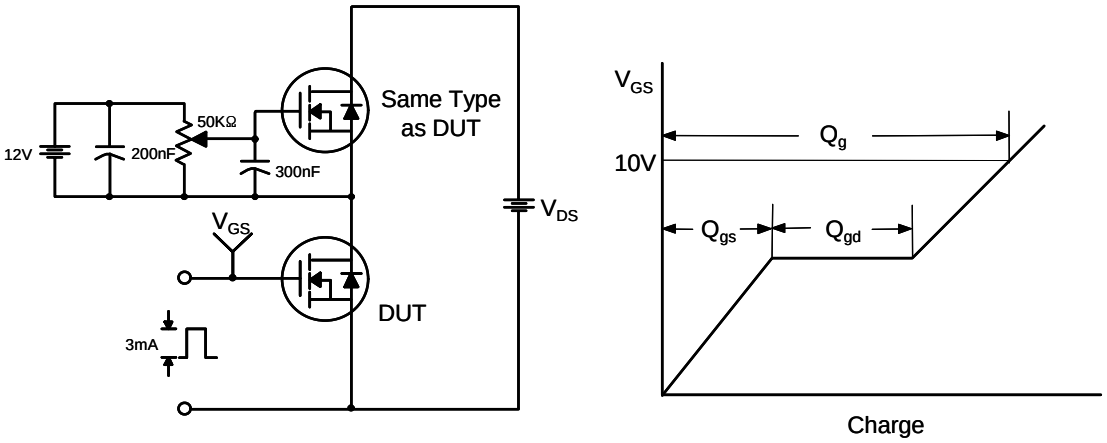


Figure 11. Transient Thermal Response Curve

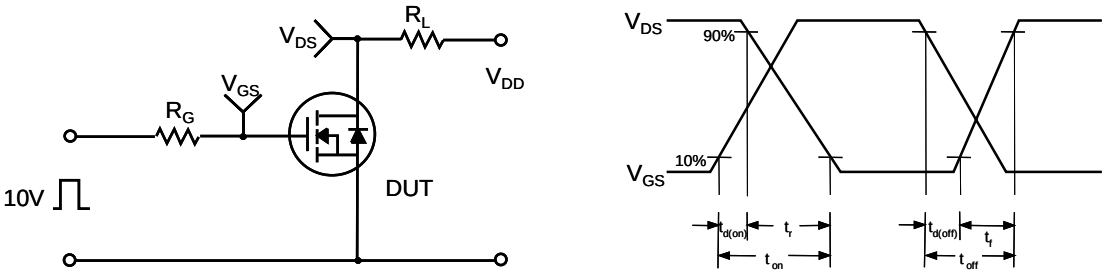
© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com

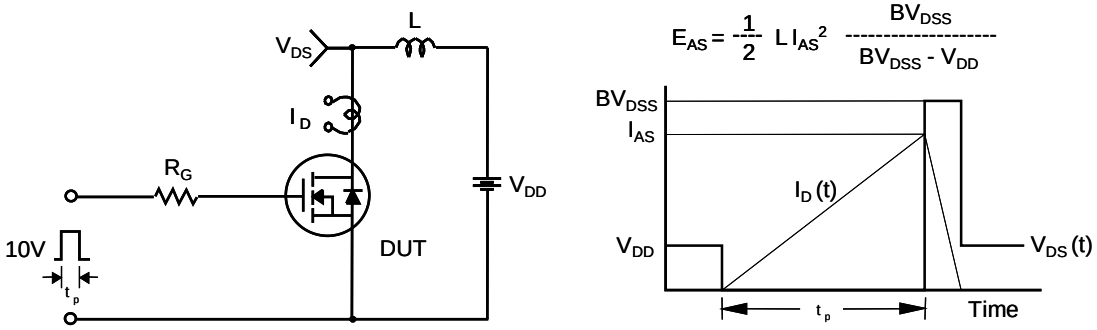
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



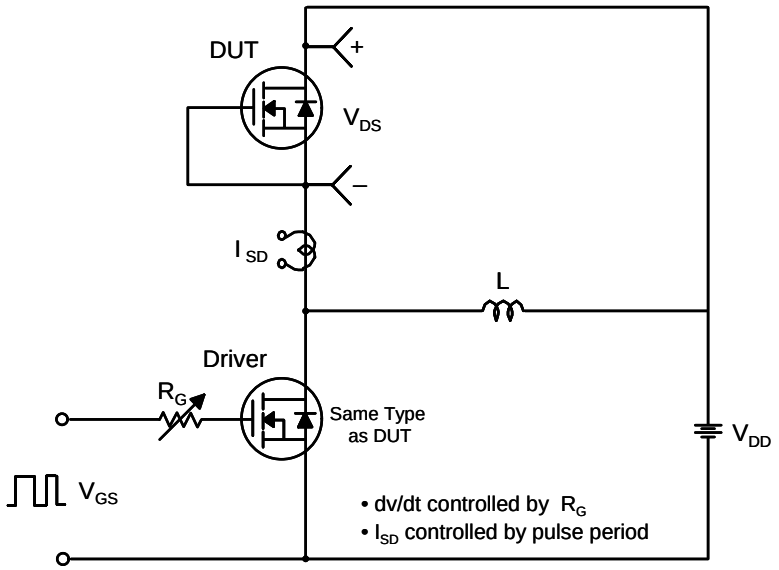
Unclamped Inductive Switching Test Circuit & Waveforms

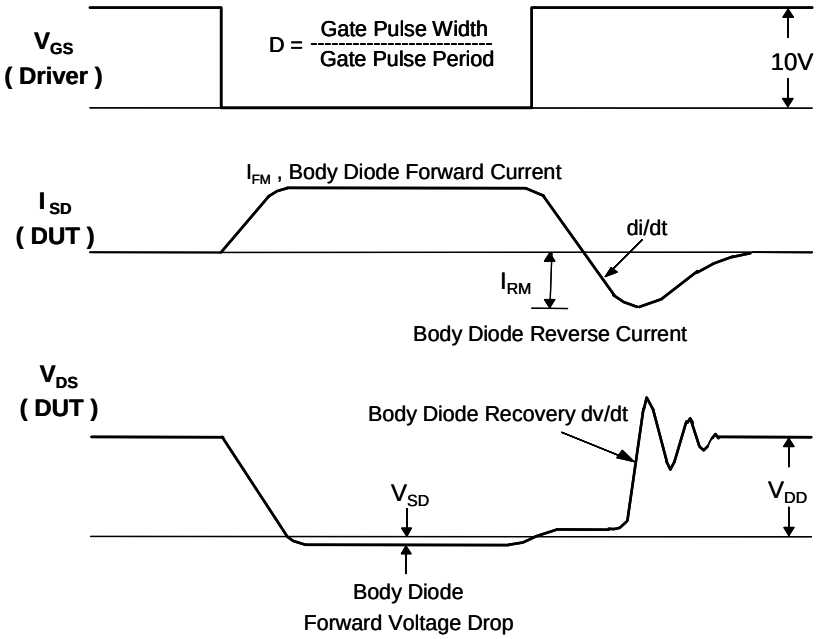


© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com

Peak Diode Recovery dv/dt Test Circuit & Waveforms





© 2006 Thinki Semiconductor Co., Ltd.

Download from alldatasheet.com